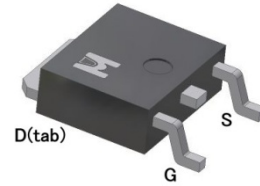


**N-Channel Logic Level Enhancement Mode Field Effect Transistor**

**Product Summary:**

|                     |             |
|---------------------|-------------|
| $BV_{DSS}$          | 15V         |
| $R_{DS(on) (MAX.)}$ | 7m $\Omega$ |
| $I_D$               | 65A         |



UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free



**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$  Unless Otherwise Noted)**

| PARAMETERS/TEST CONDITIONS                     |  | SYMBOL           | LIMITS     | UNIT             |
|--|--|------------------|------------|------------------|
| Gate-Source Voltage                            |  | $V_{GS}$         | $\pm 8$    | V                |
| Continuous Drain Current                       | $T_C = 25^\circ\text{C}$                             | $I_D$            | 65         | A                |
|  | $T_C = 100^\circ\text{C}$                            |                  | 41         |                  |
| Pulsed Drain Current <sup>1</sup>              |  | $I_{DM}$         | 160        |                  |
| Avalanche Current                              |  | $I_{AS}$         | 35         |                  |
| Avalanche Energy                               | $L = 0.1\text{mH}, I_D = 35\text{A}, R_G = 25\Omega$ | $E_{AS}$         | 61.25      | mJ               |
| Power Dissipation                              | $T_C = 25^\circ\text{C}$                             | $P_D$            | 50         | W                |
|  | $T_C = 100^\circ\text{C}$                            |                  | 20         |                  |
| Operating Junction & Storage Temperature Range |  | $T_{j}, T_{stg}$ | -55 to 150 | $^\circ\text{C}$ |

100% UIS testing in condition of  $V_D = 15\text{V}$ ,  $L = 0.1\text{mH}$ ,  $V_G = 10\text{V}$ ,  $I_L = 20\text{A}$ , Rated  $V_{DS} = 15\text{V}$  N-CH

**THERMAL RESISTANCE RATINGS**

| THERMAL RESISTANCE               | SYMBOL          | TYPICAL | MAXIMUM | UNIT                        |
|----------------------------------|-----------------|---------|---------|-----------------------------|
| Junction-to-Case                 | $R_{\theta JC}$ |         | 2.5     | $^\circ\text{C} / \text{W}$ |
| Junction-to-Ambient <sup>3</sup> | $R_{\theta JA}$ |         | 75      |                             |

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>Duty cycle  $\leq 1\%$

<sup>3</sup>75 $^\circ\text{C} / \text{W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.

**ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25 °C, Unless Otherwise Noted)**

| PARAMETER   | SYMBOL               | TEST CONDITIONS   | LIMITS |      |      | UNIT |
|---|----------------------|---|--------|------|------|------|
|   |                      |   | MIN    | TYP  | MAX  |      |
| <b>STATIC</b>   |                      |   |        |      |      |      |
| Drain-Source Breakdown Voltage  | V <sub>(BR)DSS</sub> | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA  | 15     |      |      | V    |
| Gate Threshold Voltage  | V <sub>GS(th)</sub>  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                                  | 0.35   | 0.6  | 0.9  |      |
| Gate-Body Leakage   | I <sub>GSS</sub>     | V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±8V   |        |      | ±100 | nA   |
| Zero Gate Voltage Drain Current   | I <sub>DSS</sub>     | V <sub>DS</sub> = 12V, V <sub>GS</sub> = 0V   |        |      | 1    | μA   |
|   |                      | V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125 °C                        |        |      | 10   |      |
| On-State Drain Current <sup>1</sup>   | I <sub>D(ON)</sub>   | V <sub>DS</sub> = 5V, V <sub>GS</sub> = 4.5V  | 65     |      |      | A    |
| Drain-Source On-State Resistance <sup>1</sup>                                 | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 18A  |        | 5.8  | 7    | mΩ   |
|   |                      | V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 15A  |        | 6.5  | 8    |      |
|   |                      | V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 10A  |        | 7.5  | 10   |      |
| Forward Transconductance <sup>1</sup>   | g <sub>fs</sub>      | V <sub>DS</sub> = 5V, I <sub>D</sub> = 18A  |        | 22   |      | S    |
| <b>DYNAMIC</b>  |                      |   |        |      |      |      |
| Input Capacitance   | C <sub>iss</sub>     | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 10V, f = 1MHz                                       |        | 2091 |      | pF   |
| Output Capacitance  | C <sub>oss</sub>     |   |        | 250  |      |      |
| Reverse Transfer Capacitance  | C <sub>rss</sub>     |   |        | 172  |      |      |
| Gate Resistance   | R <sub>g</sub>       | V <sub>GS</sub> = 15mV, V <sub>DS</sub> = 0V, f = 1MHz                                      |        | 1.8  |      | Ω    |
| Total Gate Charge <sup>1,2</sup>  | Q <sub>g</sub>       | V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V,<br>I <sub>D</sub> = 18A                      |        | 19   |      | nC   |
| Gate-Source Charge <sup>1,2</sup>   | Q <sub>gs</sub>      |   |        | 2.3  |      |      |
| Gate-Drain Charge <sup>1,2</sup>  | Q <sub>gd</sub>      |   |        | 4    |      |      |
| Turn-On Delay Time <sup>1,2</sup>   | t <sub>d(on)</sub>   | V <sub>DS</sub> = 10V,<br>I <sub>D</sub> = 1A, V <sub>GS</sub> = 4.5V, R <sub>GS</sub> = 6Ω |        | 10   |      | nS   |
| Rise Time <sup>1,2</sup>  | t <sub>r</sub>       |   |        | 15   |      |      |
| Turn-Off Delay Time <sup>1,2</sup>  | t <sub>d(off)</sub>  |   |        | 50   |      |      |
| Fall Time <sup>1,2</sup>  | t <sub>f</sub>       |   |        | 18   |      |      |
| <b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>C</sub> = 25 °C)</b> |                      |   |        |      |      |      |
| Continuous Current  | I <sub>S</sub>       |   |        |      | 65   | A    |
| Forward Voltage <sup>1</sup>  | V <sub>SD</sub>      | I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0V                                      |        |      | 1.3  | V    |
| Reverse Recovery Time   | t <sub>rr</sub>      |   |        | 30   |      | nS   |
| Reverse Recovery Charge   | Q <sub>rr</sub>      |   |        | 20   |      | nC   |

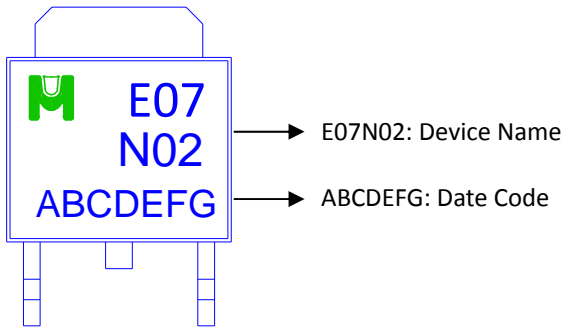
<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

<sup>2</sup>Independent of operating temperature.

<sup>3</sup>Pulse width limited by maximum junction temperature.

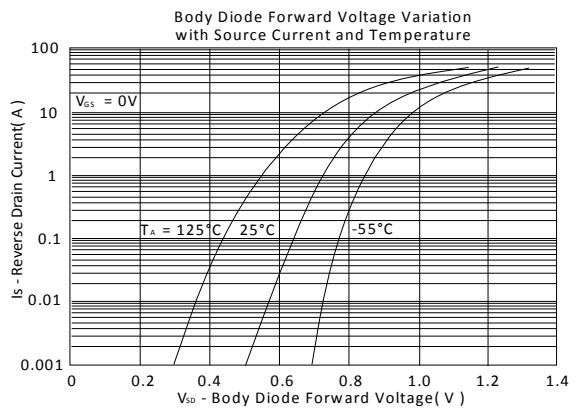
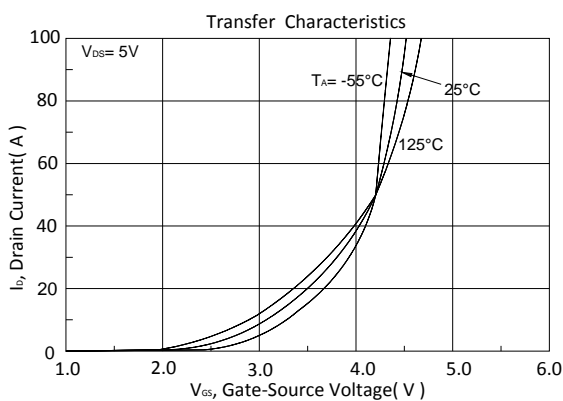
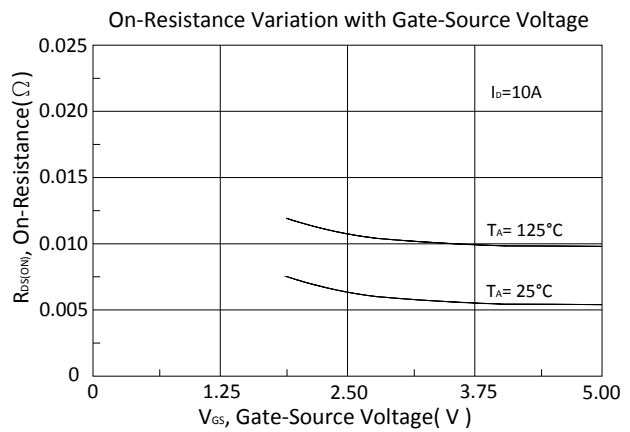
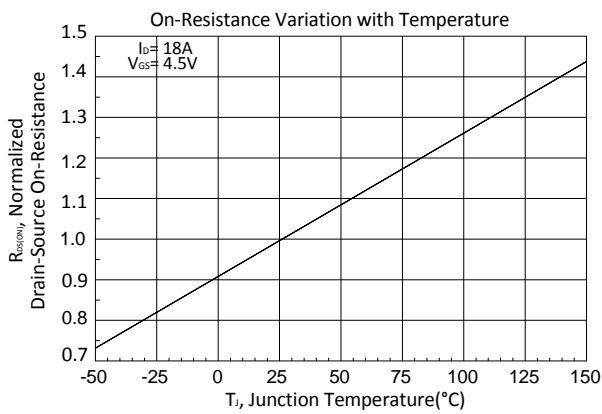
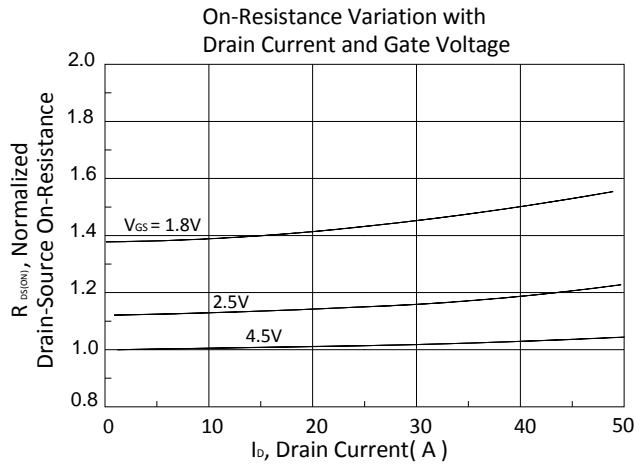
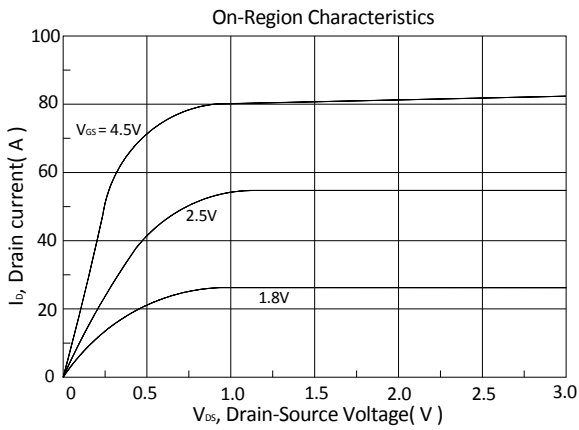
Ordering & Marking Information:

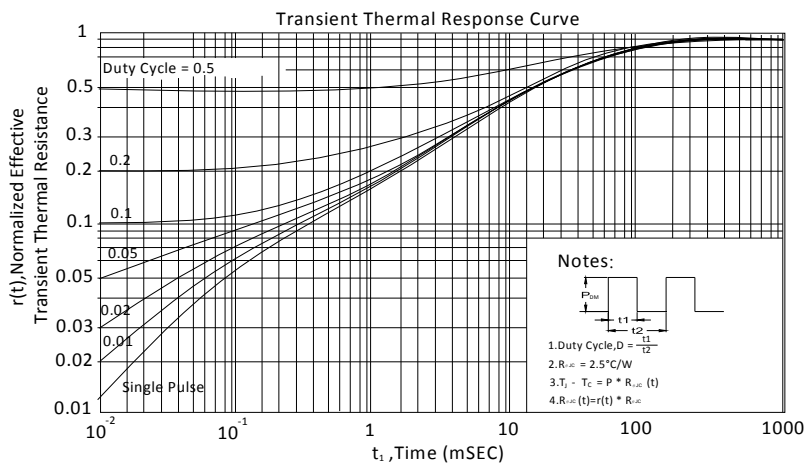
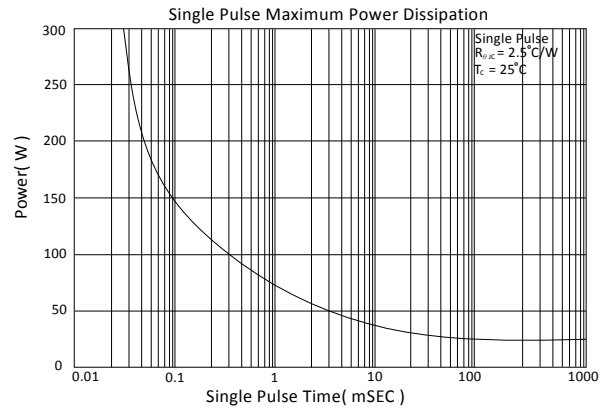
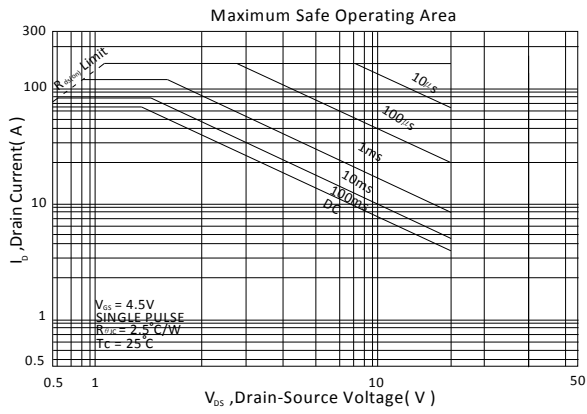
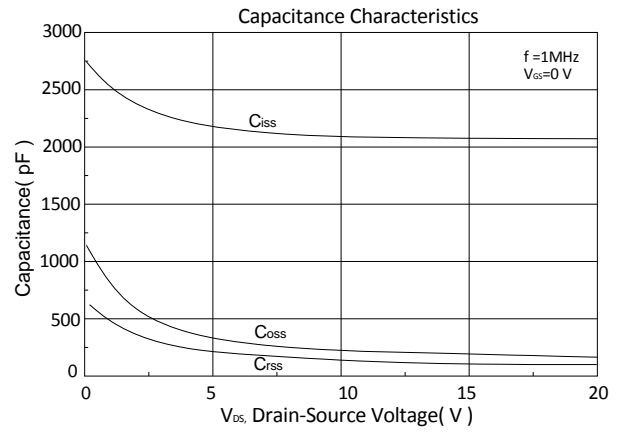
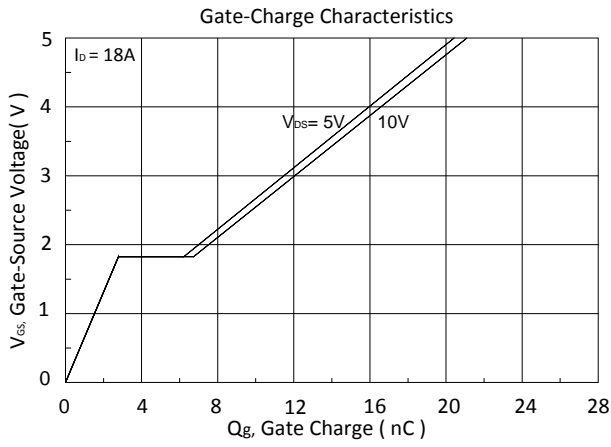
Device Name: EME07N02A for DPAK (TO-252)





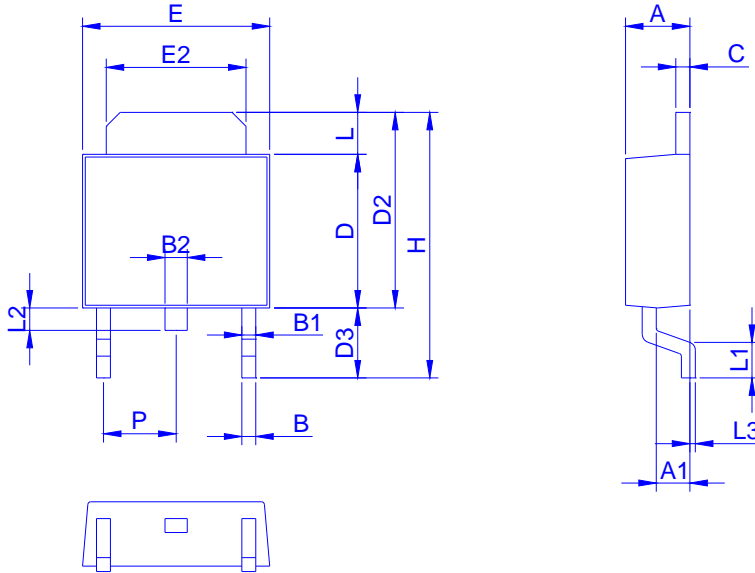
TYPICAL CHARACTERISTICS







Outline Drawing



| Dimension | A    | A1   | B    | B1   | B2   | C    | D    | D2   | D3   | E    | E2   | H     | L    | L1   | L2   | L3   | P    |
|-----------|------|------|------|------|------|------|------|------|------|------|------|-------|------|------|------|------|------|
| Min.      | 2.10 | 0.95 | 0.30 | 0.40 | 0.60 | 0.40 | 5.30 | 6.70 | 2.20 | 6.40 | 4.80 | 9.20  | 0.89 | 0.90 | 0.50 | 0.00 | 2.10 |
| Max.      | 2.50 | 1.30 | 0.85 | 0.94 | 1.00 | 0.60 | 6.20 | 7.30 | 3.00 | 6.70 | 5.45 | 10.15 | 1.70 | 1.65 | 1.10 | 0.30 | 2.50 |

Footprint

